

Supplementary Information

for

High-refractive index and mechanically cleavable non-van der Waals InGaS₃

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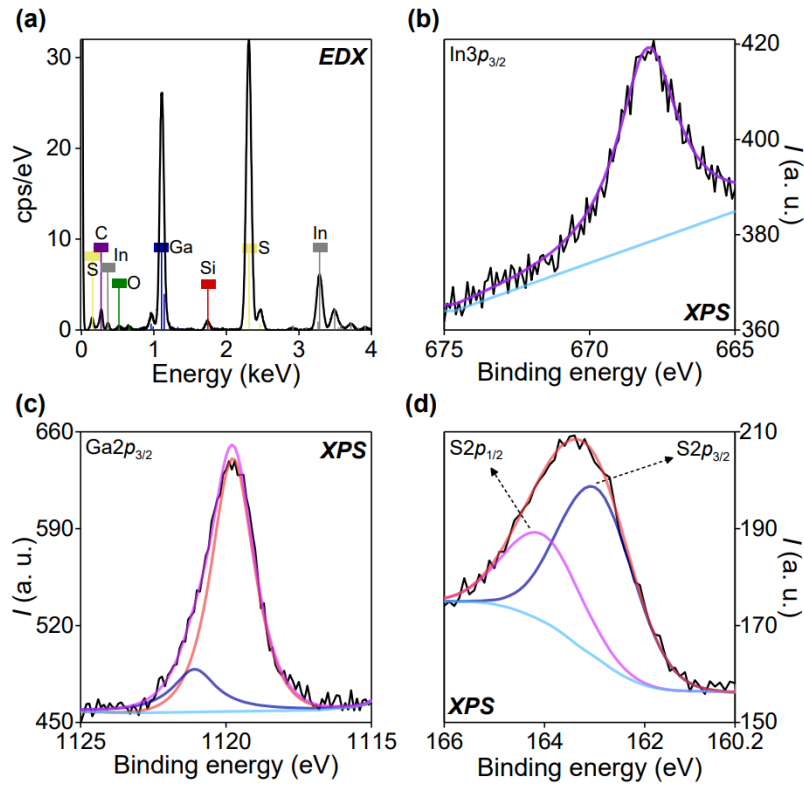
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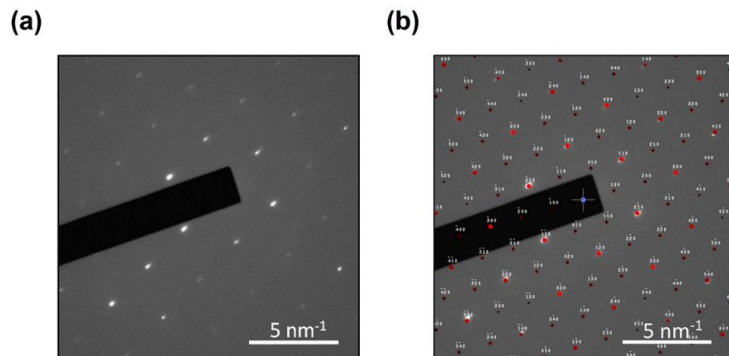
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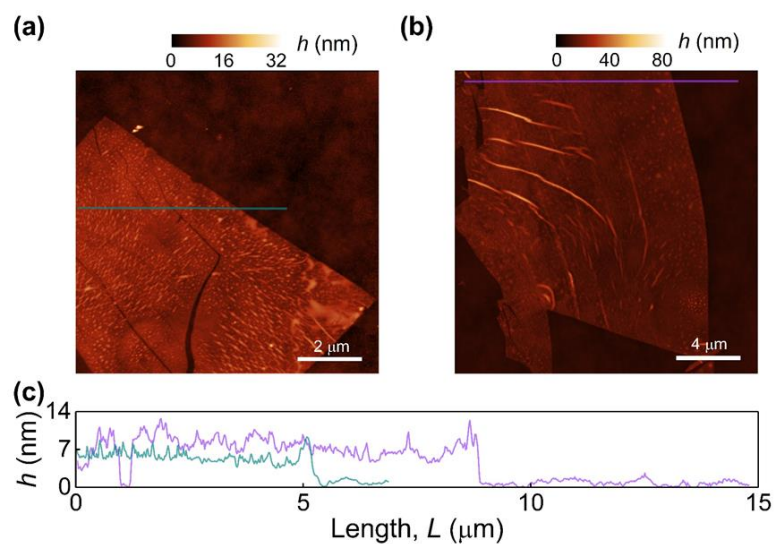
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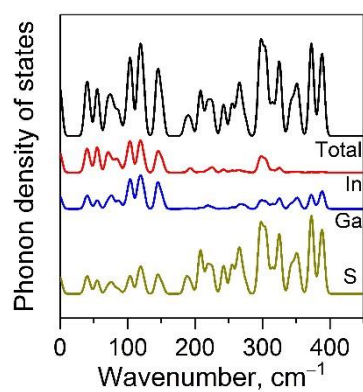
Supplementary Figure 1: EDX and XPS patterns of InGaS₃ exfoliated sheets on Si/SiO₂ substrate. **a** EDX pattern. Element ratio 22 (± 2.6) : 20.7 (± 1.8) : 57.3 (± 1.5) for In:Ga:S. **b-d** Core level XPS spectra corresponding to In (b), Ga (c) and S (d) atoms. Black lines represent raw spectra and coloured ones correspond to deconvoluted peaks on top of smooth background (light blue lines). Element ratio 18:24:58 for In:Ga:S.



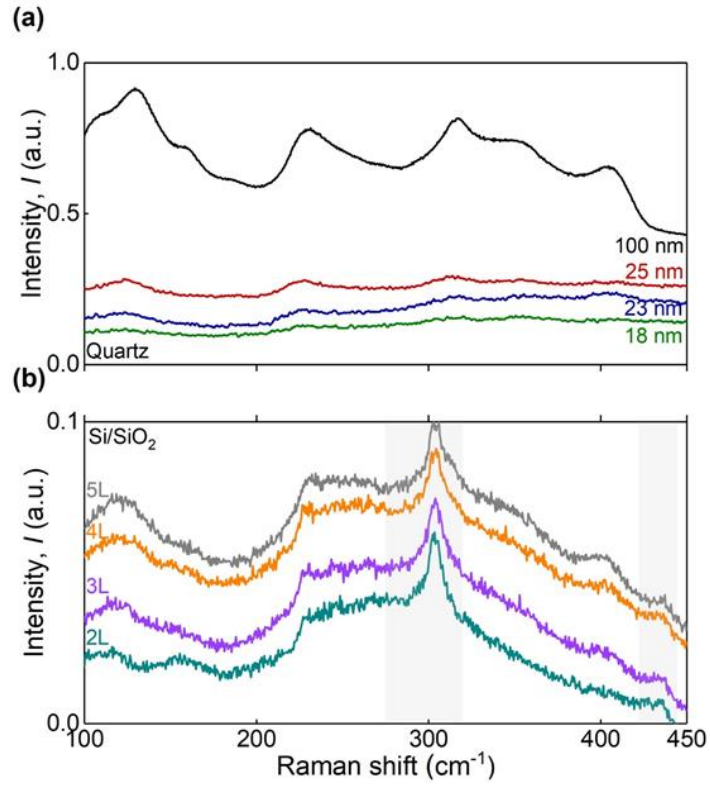
Supplementary Figure 2: TEM patterns InGaS₃ exfoliated sheets on standard grids: **a** experimental diffraction pattern across a^*b^* plane. **b** Simulated Miller index pattern on top of the experimental micrograph presented in (a).



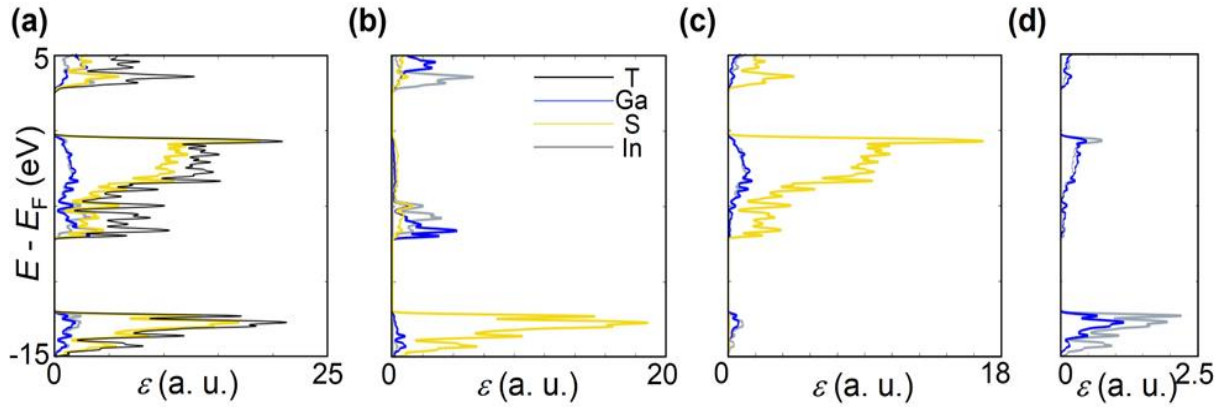
Supplementary Figure 3: AFM images of inhomogeneous atomic sheets of InGaS_3 . a and b topography micrographs of typical ultrathin sheets. c Height histogram taken along green (a) and purple (b) lines presented in (a) and (b).



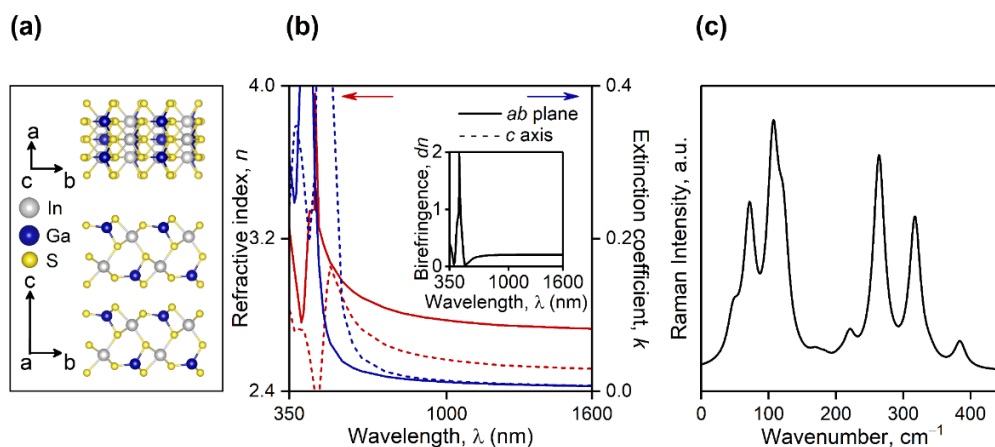
Supplementary Figure 4: Partial phonon density of states of hexagonal phase of InGaS_3 . Black line represents the total phonon density of states, the coloured ones correspond to the contribution from each of the elements: In (red), Ga (blue), yellow (S).



Supplementary Figure 5: Raman spectra of thin InGaS₃ sheets placed on various substrates. a Quartz, and **b** Si/SiO₂ substrates. Grey shaded regions correspond to Si modes. Measurements performed at 532 nm.



Supplementary Figure 6: eDOS obtained via HSE. a Total spectrum: partial eDOS calculated by orbitals. **b** s-orbital. **c** p-orbital. **d** d-orbital. E_F is shifted to zero for clarity throughout the figure. Grey lines correspond to the contribution of In, blue – Ga, yellow – S atoms, and black ones, to the total eDoS throughout the figure



Supplementary Figure 7: Orthorhombic phase of InGaS_3 obtained through first-principle calculations. **a** Space group: $\text{Pmn}2_1$, lattice constants: $a = 6.21 \text{ \AA}$ and $b = 3.78 \text{ \AA}$. **b** Refractive index and extinction coefficient for ab -plane (straight line) and c -axis (dashed line) with non-zero absorption in the entire considered range obtained by HSE. The inset shows material's birefringence. **c** Evaluated Raman spectrum for the orthorhombic InGaS_3 .

Formula	InGaS_3
Formula weight (g/mol)	280.72
Diffractometer	Bruker D8 Quest
X-ray source	Micro-focus Mo $K\alpha$ tube
Data collection method	ω scans
Temperature (K)	100
Crystal system	Hexagonal
Space group	P6_5
a ($\text{\AA}$)	6.6309(3)
b ($\text{\AA}$)	6.6309(3)
c ($\text{\AA}$)	17.9293(9)
α ($^\circ$)	90
β ($^\circ$)	90

γ (°)	120
V (Å ³)	682.71(7)
Z	6
Color, habit	Yellow, block
Crystal dimensions (mm)	0.020 × 0.033 × 0.035
Density D_{calc} (g·cm ⁻³)	4.097
μ (mm ⁻¹)	12.151
Unique reflections (R_{int})	1194 (0.0472)
Observed reflections [$I > 2\sigma(I)$]	1165
Parameters	47
$R_1[I > 2\sigma(I)]$, ωR_2	0.0249, 0.0587
Goodness of fit on F^2	1.151
Absorption correction	multi-scan
T_{min} , T_{max}	0.6522, 0.7473
ρ_{min} , ρ_{max} (eÅ ⁻³)	-0.713, 1.638

Supplementary Table 1: Summary of data collection and structure refinement details for hexagonal phase of InGaS₃.

Parameter	Distance, Å
Ga1 – S1	2.2494(14)
Ga1 – S3	2.2533(16)
Ga1 – S2	2.2890(16)
Ga1 – S2 ⁱ	2.323(2)
S1 – In1	2.4323(19)

S1 – In1 ⁱⁱ	2.745(2)
S2 – In1 ⁱⁱⁱ	2.4883(18)
S3 – In1 ^{iv}	2.4549(17)
S3 – In1 ^v	2.6703(19)

Supplementary Table 2: Selected interatomic distances of hexagonal phase of InGaS₃. Symmetry codes: (i) x-y, x, z-1/6; (ii) x-y+1, x, z-1/6; (iii) x, y-1, z; (iv) x-1, y-1, z; (v) y-1, -x+y, z+1/6.

No	A (T.O.)	A (L.O.)	B	E ₁ (T.O.)	E ₂
1	383.5	391.1	388.4	389.9	387.8
2	371.0	375.9	372.0	373.3	372.2
3	341.5	351.3	342.9	353.6	349.3
4	314.2	323.0	324.8	322.8	325.6
5	304.1	305.1	314.5	304.3	305.5
6	297.3	297.3	295.3	298.4	296.7
7	255.0	270.2	274.9	264.1	268.2
8	192.7	226.0	255.0	225.1	242.5
9	186.5	186.6	209.7	207.1	218.7
10	151.5	151.7	151.2	145.4	144.0
11	105.7	106.5	122.6	118.5	123.8
12	88.5	89.5	115.8	105.7	118.6
13	45.2	45.2	98.7	78.8	103.3
14	39.6	39.6	83.6	55.5	71.2
15			56.8		41.5

Supplementary Table 3: Calculated wavenumbers of vibrational modes of hexagonal phase of InGaS₃. Units are in cm⁻¹.

Crystallographic Information File (CIF) of hexagonal phase of InGaS₃ crystal structure used in first-principle calculations

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#-----
# InGaS3 crystal
#-----
_cell_length_a      6.6152940
_cell_length_b      6.6152940
_cell_length_c      17.753407
_cell_angle_alpha    90.000000
_cell_angle_beta     90.000000
_cell_angle_gamma    120.00000
_cell_volume         672.838179
_space_group_name_H-M_alt  'P 1'
_space_group_IT_number 1
loop_
_space_group_symop_operation_xyz
'x, y, z'
loop_
_atom_site_label
_atom_site_occupancy
_atom_site_fract_x
_atom_site_fract_y
_atom_site_fract_z
_atom_site_adp_type
_atom_site_U_iso_or_equiv
_atom_site_type_symbol
In1  1.0  0.668420  0.992314  0.154321  Uiso  ? In
In2  1.0  0.007686  0.676106  0.820987  Uiso  ? In
In3  1.0  0.323894  0.331580  0.487654  Uiso  ? In
In4  1.0  0.331580  0.007686  0.654321  Uiso  ? In
In5  1.0  0.992314  0.323894  0.320987  Uiso  ? In
In6  1.0  0.676106  0.668420  0.987654  Uiso  ? In
Ga1  1.0  0.319414  0.326485  0.126589  Uiso  ? Ga
Ga2  1.0  0.673515  0.992929  0.793255  Uiso  ? Ga
Ga3  1.0  0.007071  0.680586  0.459922  Uiso  ? Ga
Ga4  1.0  0.680586  0.673515  0.626589  Uiso  ? Ga
Ga5  1.0  0.326485  0.007071  0.293255  Uiso  ? Ga
Ga6  1.0  0.992929  0.319414  0.959922  Uiso  ? Ga
S1  1.0  0.689371  0.628974  0.138550  Uiso  ? S
S2  1.0  0.371026  0.060397  0.805217  Uiso  ? S
S3  1.0  0.939603  0.310629  0.471883  Uiso  ? S
S4  1.0  0.310629  0.371026  0.638550  Uiso  ? S
S5  1.0  0.628974  0.939603  0.305217  Uiso  ? S
S6  1.0  0.060397  0.689371  0.971883  Uiso  ? S
S7  1.0  0.277257  0.976053  0.163639  Uiso  ? S
S8  1.0  0.023947  0.301204  0.830306  Uiso  ? S
S9  1.0  0.698796  0.722743  0.496973  Uiso  ? S
S10 1.0  0.722743  0.023947  0.663639  Uiso  ? S
S11 1.0  0.976053  0.698796  0.330306  Uiso  ? S
S12 1.0  0.301204  0.277257  0.996973  Uiso  ? S
S13 1.0  0.029602  0.380062  0.170811  Uiso  ? S
S14 1.0  0.619938  0.649540  0.837478  Uiso  ? S
S15 1.0  0.350460  0.970398  0.504145  Uiso  ? S
S16 1.0  0.970398  0.619938  0.670811  Uiso  ? S
S17 1.0  0.380062  0.350460  0.337478  Uiso  ? S
S18 1.0  0.649540  0.029602  0.004145  Uiso  ? S
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